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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f415vgt6

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The DMA can be used with the main peripherals:

- SPI and I²S
- I²C
- USART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDIO
- Cryptographic acceleration
- Camera interface (DCMI)
- ADC.

2.2.9 Flexible static memory controller (FSMC)

The FSMC is embedded in the STM32F415xx and STM32F417xx family. It has four Chip Select outputs supporting the following modes: PCCard/Compact Flash, SRAM, PSRAM, NOR Flash and NAND Flash.

Functionality overview:

- Write FIFO
- Maximum FSMC_CLK frequency for synchronous accesses is 60 MHz.

LCD parallel interface

The FSMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

2.2.10 Nested vectored interrupt controller (NVIC)

The STM32F415xx and STM32F417xx embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 82 maskable interrupt channels plus the 16 interrupt lines of the Cortex[®]-M4 with FPU core.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

The STM32F417xx includes the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors (see the STM32F40xxx/41xxx reference manual for details)
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes.
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 2008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time

2.2.29 Controller area network (bxCAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bitrate up to 1 Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOs with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). 256 bytes of SRAM are allocated for each CAN.

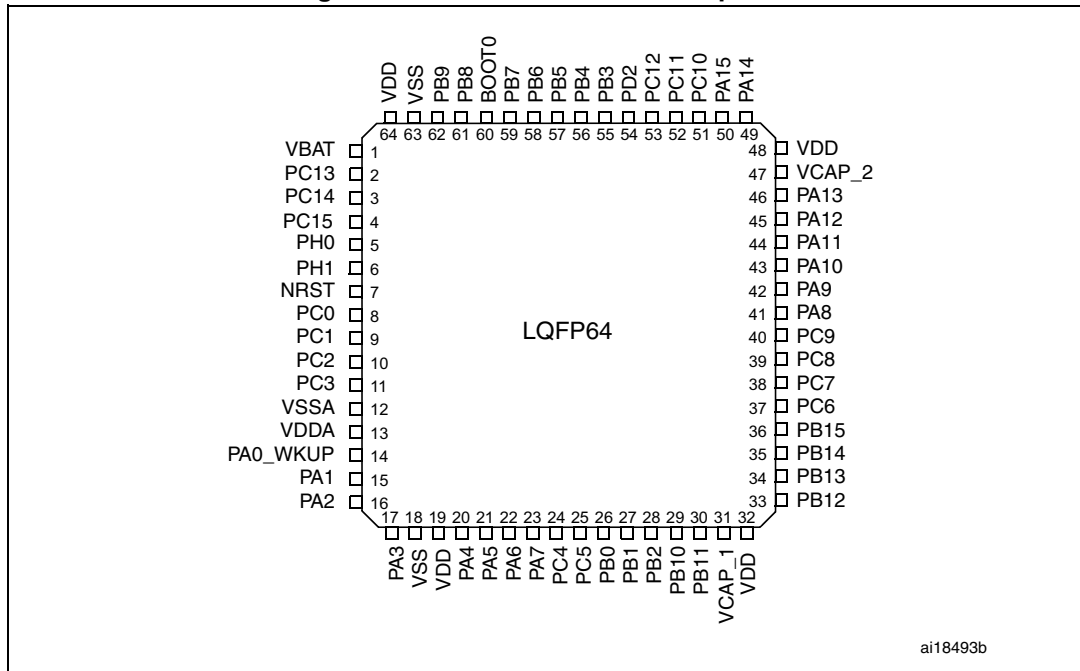
2.2.30 Universal serial bus on-the-go full-speed (OTG_FS)

The STM32F415xx and STM32F417xx embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator. The major features are:

- Combined Rx and Tx FIFO size of 320 × 35 bits with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 4 bidirectional endpoints
- 8 host channels with periodic OUT support
- HNP/SNP/IP inside (no need for any external resistor)
- For OTG/Host modes, a power switch is needed in case bus-powered devices are connected

3 Pinouts and pin description

Figure 12. STM32F41xxx LQFP64 pinout



1. The above figure shows the package top view.

Table 7. STM32F41xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
	D9			L4	48	BYPASS_REG	I	FT	-	-	-
19	E4	28	39	K4	49	V _{DD}	S	-	-	-	-
20	J9	29	40	N4	50	PA4	I/O	TTa	(4)	SPI1_NSS / SPI3_NSS / USART2_CK / DCMI_HSYNC / OTG_HS_SOF / I2S3_WS / EVENTOUT	ADC12_IN4 /DAC_OUT1
21	G8	30	41	P4	51	PA5	I/O	TTa	(4)	SPI1_SCK / OTG_HS_ULPI_CK / TIM2_CH1_ETR / TIM8_CH1N / EVENTOUT	ADC12_IN5/DAC_ OUT2
22	H8	31	42	P3	52	PA6	I/O	FT	(4)	SPI1_MISO / TIM8_BKIN/TIM13_CH1 / DCMI_PIXCLK / TIM3_CH1 / TIM1_BKIN / EVENTOUT	ADC12_IN6
23	J8	32	43	R3	53	PA7	I/O	FT	(4)	SPI1_MOSI / TIM8_CH1N / TIM14_CH1/TIM3_CH2 / ETH_MII_RX_DV / TIM1_CH1N / ETH_RMII_CRS_DV / EVENTOUT	ADC12_IN7
24	-	33	44	N5	54	PC4	I/O	FT	(4)	ETH_RMII_RX_D0 / ETH_MII_RX_D0 / EVENTOUT	ADC12_IN14
25	-	34	45	P5	55	PC5	I/O	FT	(4)	ETH_RMII_RX_D1 / ETH_MII_RX_D1 / EVENTOUT	ADC12_IN15
26	G7	35	46	R5	56	PB0	I/O	FT	(4)	TIM3_CH3 / TIM8_CH2N / OTG_HS_ULPI_D1 / ETH_MII_RXD2 / TIM1_CH2N / EVENTOUT	ADC12_IN8
27	H7	36	47	R4	57	PB1	I/O	FT	(4)	TIM3_CH4 / TIM8_CH3N / OTG_HS_ULPI_D2 / ETH_MII_RXD3 / TIM1_CH3N / EVENTOUT	ADC12_IN9
28	J7	37	48	M6	58	PB2/BOOT1 (PB2)	I/O	FT	-	EVENTOUT	-



Table 9. Alternate function mapping (continued)

Port	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
	SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/SPI2/I2S2/I2S2ext	SPI3/I2Sext/I2S3	USART1/2/3/I2S3ext	UART4/5/USART6	CAN1/2/TIM12/13/14	OTG_FS/OTG_HS	ETH	FSMC/SDIO/OTG_FS	DCMI		
Port E	PE0	-	-	TIM4_ETR	-	-	-	-	-	-	-	-	FSMC_NBL0	DCMI_D2	-	EVENTOUT
	PE1	-	-	-	-	-	-	-	-	-	-	-	FSMC_NBL1	DCMI_D3	-	EVENTOUT
	PE2	TRACECLK	-	-	-	-	-	-	-	-	-	ETH_MII_TXD3	FSMC_A23	-	-	EVENTOUT
	PE3	TRACED0	-	-	-	-	-	-	-	-	-	-	FSMC_A19	-	-	EVENTOUT
	PE4	TRACED1	-	-	-	-	-	-	-	-	-	-	FSMC_A20	DCMI_D4	-	EVENTOUT
	PE5	TRACED2	-	-	TIM9_CH1	-	-	-	-	-	-	-	FSMC_A21	DCMI_D6	-	EVENTOUT
	PE6	TRACED3	-	-	TIM9_CH2	-	-	-	-	-	-	-	FSMC_A22	DCMI_D7	-	EVENTOUT
	PE7	-	TIM1_ETR	-	-	-	-	-	-	-	-	-	FSMC_D4	-	-	EVENTOUT
	PE8	-	TIM1_CH1N	-	-	-	-	-	-	-	-	-	FSMC_D5	-	-	EVENTOUT
	PE9	-	TIM1_CH1	-	-	-	-	-	-	-	-	-	FSMC_D6	-	-	EVENTOUT
	PE10	-	TIM1_CH2N	-	-	-	-	-	-	-	-	-	FSMC_D7	-	-	EVENTOUT
	PE11	-	TIM1_CH2	-	-	-	-	-	-	-	-	-	FSMC_D8	-	-	EVENTOUT
	PE12	-	TIM1_CH3N	-	-	-	-	-	-	-	-	-	FSMC_D9	-	-	EVENTOUT
	PE13	-	TIM1_CH3	-	-	-	-	-	-	-	-	-	FSMC_D10	-	-	EVENTOUT
	PE14	-	TIM1_CH4	-	-	-	-	-	-	-	-	-	FSMC_D11	-	-	EVENTOUT
	PE15	-	TIM1_BKIN	-	-	-	-	-	-	-	-	-	FSMC_D12	-	-	EVENTOUT

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/SPI2/I2S2/I2S2ext	SPI3/I2Sext/I2S3	USART1/2/3/I2S3ext	UART4/5/USART6	CAN1/2/TIM12/13/14	OTG_FS/OTG_HS	ETH	FSMC/SDIO/OTG_FS	DCMI		
Port G	PG0	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A10	-	-	EVENTOUT
	PG1	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A11	-	-	EVENTOUT
	PG2	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A12	-	-	EVENTOUT
	PG3	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A13	-	-	EVENTOUT
	PG4	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A14	-	-	EVENTOUT
	PG5	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A15	-	-	EVENTOUT
	PG6	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_INT2	-	-	EVENTOUT
	PG7	-	-	-	-	-	-	-	-	USART6_CK	-	-	-	FSMC_INT3	-	-	EVENTOUT
	PG8	-	-	-	-	-	-	-	-	USART6_RTS	-	-	ETH_PPS_OUT	-	-	-	EVENTOUT
	PG9	-	-	-	-	-	-	-	-	USART6_RX	-	-	-	FSMC_NE2/FSMC_NCE3	-	-	EVENTOUT
	PG10	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_NCE4_1/FSMC_NE3	-	-	EVENTOUT
	PG11	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_TX_EN ETH_RMII_TX_EN	FSMC_NCE4_2	-	-	EVENTOUT
	PG12	-	-	-	-	-	-	-	-	USART6_RTS	-	-	-	FSMC_NE4	-	-	EVENTOUT
	PG13	-	-	-	-	-	-	-	-	UART6_CTS	-	-	ETH_MII_TXD0 ETH_RMII_TXD0	FSMC_A24	-	-	EVENTOUT
	PG14	-	-	-	-	-	-	-	-	USART6_TX	-	-	ETH_MII_TXD1 ETH_RMII_TXD1	FSMC_A25	-	-	EVENTOUT
	PG15	-	-	-	-	-	-	-	-	USART6_CTS	-	-	-	-	DCMI_D13	-	EVENTOUT

Table 21. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)

Symbol	Parameter	Conditions	f _{HCLK}	Typ	Max ⁽¹⁾		Unit
				T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled ⁽³⁾⁽⁴⁾	168 MHz	93	109	117	mA
			144 MHz	76	89	96	
			120 MHz	67	79	86	
			90 MHz	53	65	73	
			60 MHz	37	49	56	
			30 MHz	20	32	39	
			25 MHz	16	27	35	
			16 MHz	11	23	30	
			8 MHz	6	18	25	
			4 MHz	4	16	23	
			2 MHz	3	15	22	
		External clock ⁽²⁾ , all peripherals disabled ⁽³⁾⁽⁴⁾	168 MHz	46	61	69	
			144 MHz	40	52	60	
			120 MHz	37	48	56	
			90 MHz	30	42	50	
			60 MHz	22	33	41	
			30 MHz	12	24	31	
			25 MHz	10	21	29	
			16 MHz	7	19	26	
			8 MHz	4	16	23	
			4 MHz	3	15	22	
			2 MHz	2	14	21	

1. Guaranteed by characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
2. External clock is 4 MHz and PLL is on when f_{HCLK} > 25 MHz.
3. When analog peripheral blocks such as (ADCs, DACs, HSE, LSE, HSI, LSI) are on, an additional power consumption should be considered.
4. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

Figure 24. Typical current consumption versus temperature, Run mode, code with data processing running from Flash (ART accelerator ON) or RAM, and peripherals OFF

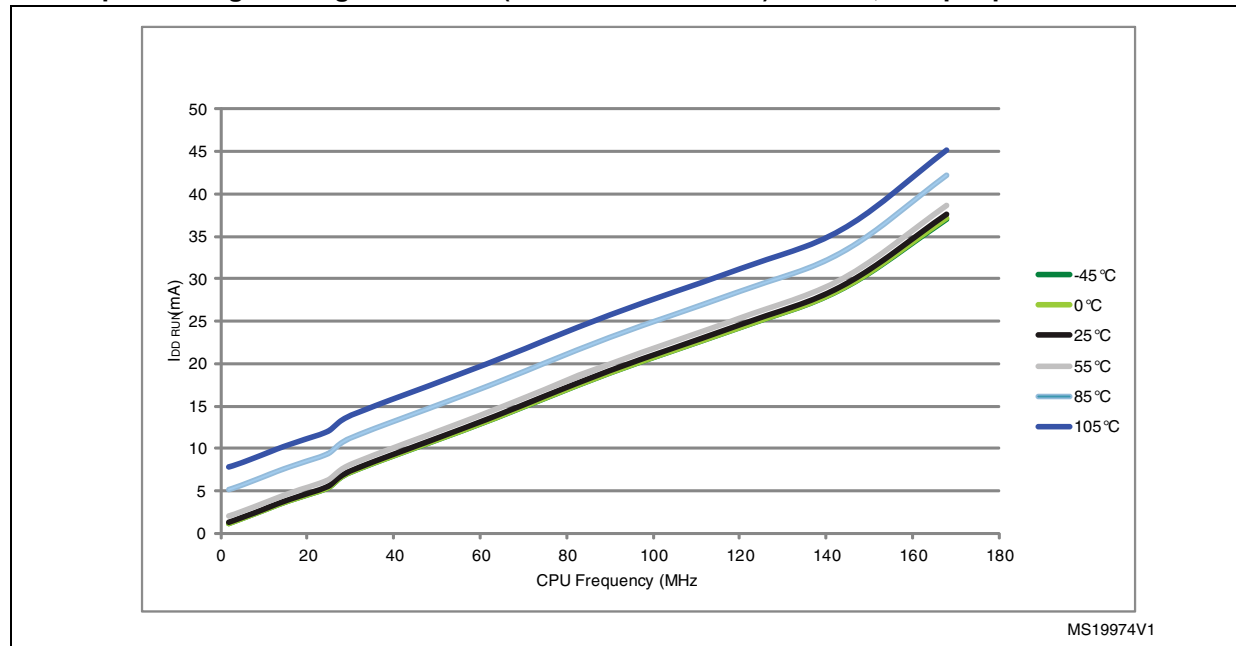
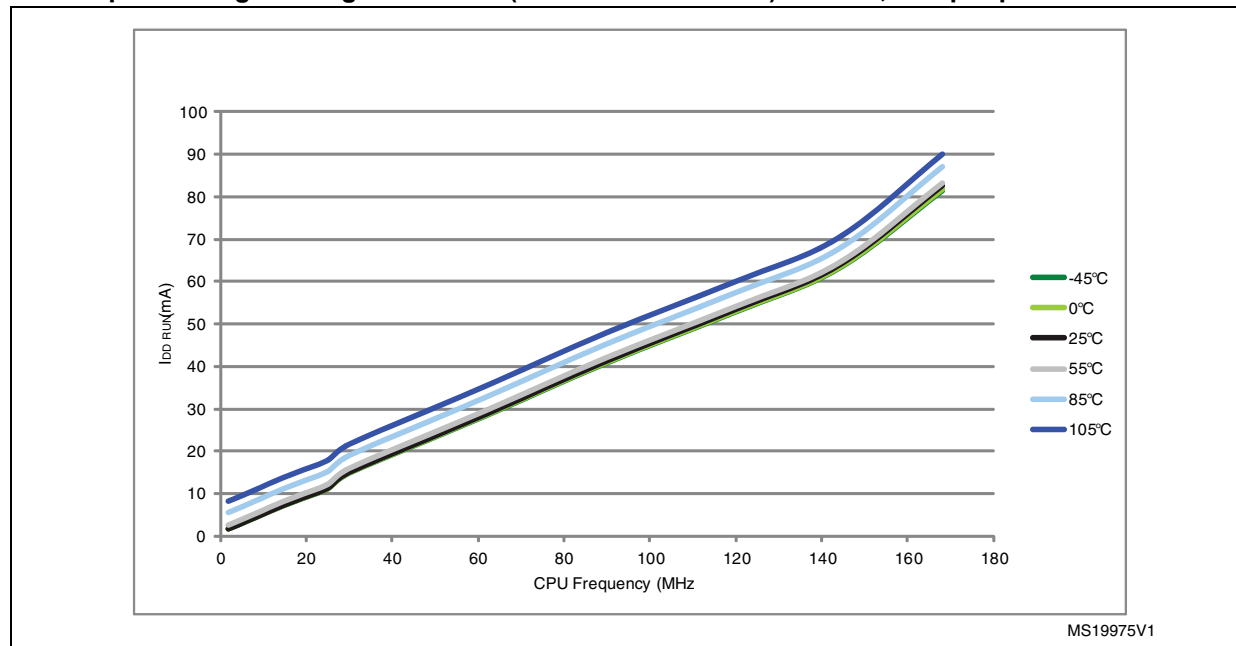


Figure 25. Typical current consumption versus temperature, Run mode, code with data processing running from Flash (ART accelerator ON) or RAM, and peripherals ON



Low-speed external user clock generated from an external source

The characteristics given in [Table 31](#) result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 14](#).

Table 31. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User External clock source frequency ⁽¹⁾	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{f(LSE)}$	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance ⁽¹⁾	-	-	5	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	30	-	70	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design.

Figure 30. High-speed external clock source AC timing diagram

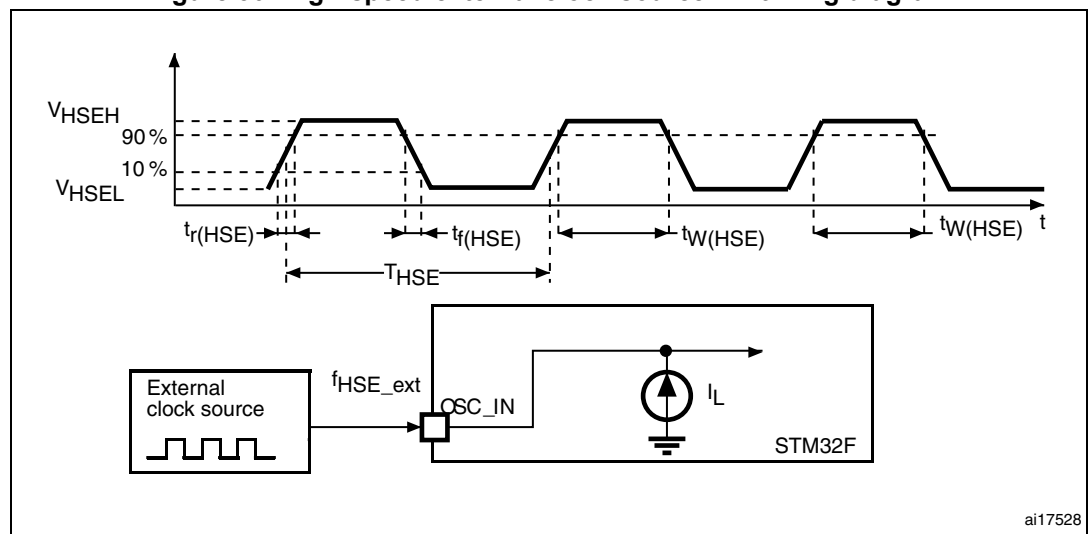
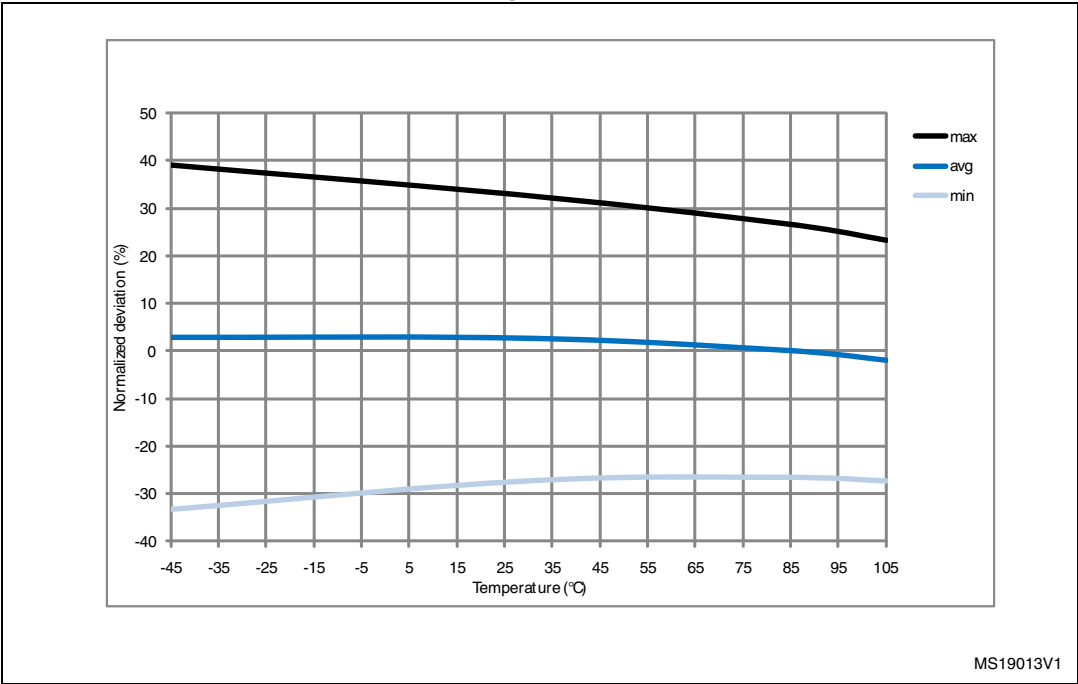


Figure 34. ACC_{LSI} versus temperature



MS19013V1

5.3.10 PLL characteristics

The parameters given in [Table 36](#) and [Table 37](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

Table 36. Main PLL characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock ⁽¹⁾	-	0.95 ⁽²⁾	1	2.10	MHz
f_{PLL_OUT}	PLL multiplier output clock	-	24	-	168	MHz
f_{PLL48_OUT}	48 MHz PLL multiplier output clock	-	-	48	75	MHz
f_{VCO_OUT}	PLL VCO output	-	100	-	432	MHz
t_{LOCK}	PLL lock time	VCO freq = 100 MHz	75	-	200	μs
		VCO freq = 432 MHz	100	-	300	

Table 41. Flash memory programming with V_{PP}

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
t_{prog}	Double word programming	$T_A = 0 \text{ to } +40 \text{ }^\circ\text{C}$ $V_{DD} = 3.3 \text{ V}$ $V_{PP} = 8.5 \text{ V}$	-	16	100 ⁽²⁾	μs
$t_{ERASE16KB}$	Sector (16 KB) erase time		-	230	-	ms
$t_{ERASE64KB}$	Sector (64 KB) erase time		-	490	-	
$t_{ERASE128KB}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	6.9	-	s
V_{prog}	Programming voltage	-	2.7	-	3.6	V
V_{PP}	V_{PP} voltage range	-	7	-	9	V
I_{PP}	Minimum current sunk on the V_{PP} pin	-	10	-	-	mA
t_{VPP} ⁽³⁾	Cumulative time during which V_{PP} is applied	-	-	-	1	hour

1. Guaranteed by design.

2. The maximum programming time is measured after 100K erase operations.

3. V_{PP} should only be connected during programming/erasing.

Table 42. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min ⁽¹⁾	
N_{END}	Endurance	$T_A = -40 \text{ to } +85 \text{ }^\circ\text{C}$ (6 suffix versions) $T_A = -40 \text{ to } +105 \text{ }^\circ\text{C}$ (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle ⁽²⁾ at $T_A = 85 \text{ }^\circ\text{C}$	30	Years
		1 kcycle ⁽²⁾ at $T_A = 105 \text{ }^\circ\text{C}$	10	
		10 kcycles ⁽²⁾ at $T_A = 55 \text{ }^\circ\text{C}$	20	

1. Guaranteed by characterization.

2. Cycling performed over the whole temperature range.

5.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB:** A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

Table 55. SPI dynamic characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{w(SCKH)}$	SCK high and low time	Master mode, SPI presc = 2, $2.7V < V_{DD} < 3.6V$	$T_{PCLK}-0.5$	T_{PCLK}	$T_{PCLK}+0.5$	ns
$t_{w(SCKL)}$		Master mode, SPI presc = 2, $1.7V < V_{DD} < 3.6V$	$T_{PCLK}-2$	T_{PCLK}	$T_{PCLK}+2$	
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$4 \times T_{PCLK}$	-	-	
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	$2 \times T_{PCLK}$	-	-	
$t_{su(MI)}$	Data input setup time	Master mode	6.5	-	-	
$t_{su(SI)}$		Slave mode	2.5	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	2.5	-	-	
$t_{h(SI)}$		Slave mode	4	-	-	
$t_{a(SO)}^{(2)}$	Data output access time	Slave mode, SPI presc = 2	0	-	$4 \times T_{PCLK}$	
$t_{dis(SO)}^{(3)}$	Data output disable time	Slave mode, SPI1, $2.7V < V_{DD} < 3.6V$	0	-	7.5	
		Slave mode, SPI1/2/3 $1.7V < V_{DD} < 3.6V$	0	-	16.5	
$t_{v(SO)}$ $t_{h(SO)}$	Data output valid/hold time	Slave mode (after enable edge), SPI1, $2.7V < V_{DD} < 3.6V$	-	11	13	
		Slave mode (after enable edge), SPI2/3, $2.7V < V_{DD} < 3.6V$	-	12	16.5	
		Slave mode (after enable edge), SPI1, $1.7V < V_{DD} < 3.6V$	-	15.5	19	
		Slave mode (after enable edge), SPI2/3, $1.7V < V_{DD} < 3.6V$	-	18	20.5	
$t_{v(MO)}$	Data output valid time	Master mode (after enable edge), SPI1, $2.7V < V_{DD} < 3.6V$	-	-	2.5	
		Master mode (after enable edge), SPI1/2/3, $1.7V < V_{DD} < 3.6V$	-	-	4.5	
$t_{h(MO)}$	Data output hold time	Master mode (after enable edge)	0	-	-	

1. Guaranteed by characterization.

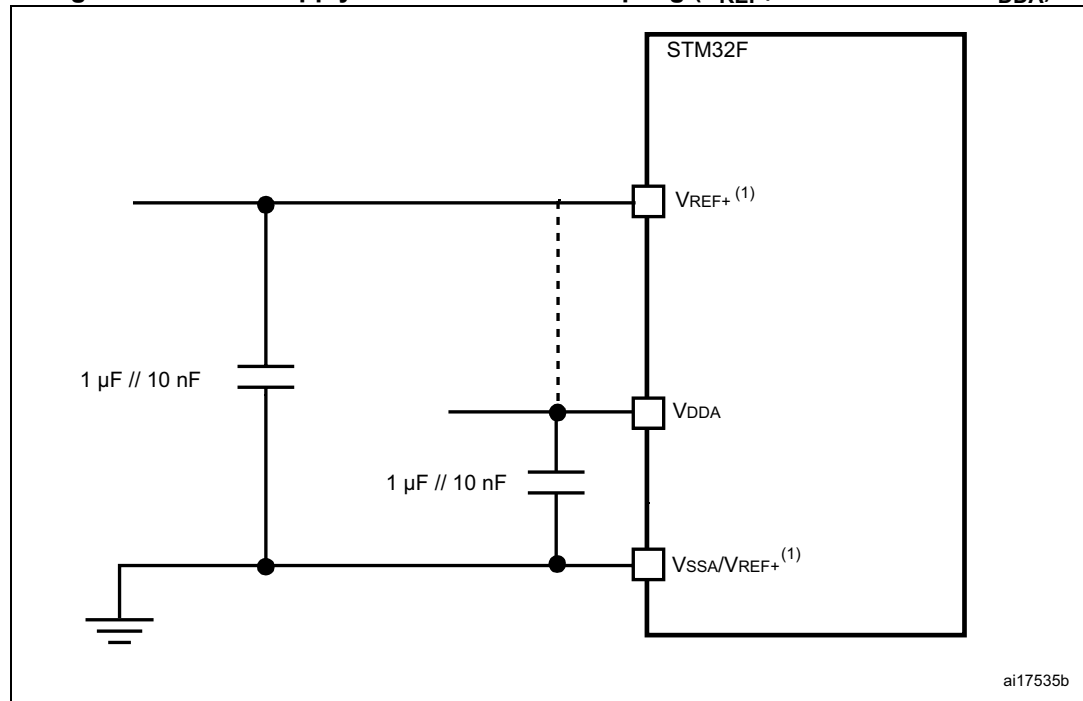
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.

3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.

General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 51](#) or [Figure 52](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

Figure 51. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176. V_{REF+} is also available on LQFP100, LQFP144, and LQFP176. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA} .

5.3.23 V_{BAT} monitoring characteristics

Table 71. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	50	-	K Ω
Q	Ratio on V_{BAT} measurement	-	2	-	
Er ⁽¹⁾	Error on Q	-1	-	+1	%
T _{S_vbat} ⁽²⁾⁽²⁾	ADC sampling time when reading the V_{BAT} 1 mV accuracy	5	-	-	μ s

1. Guaranteed by design.

2. Shortest sampling time can be determined in the application by multiple iterations.

5.3.24 Embedded reference voltage

The parameters given in [Table 72](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

Table 72. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{REFINT}	Internal reference voltage	-40 °C < T _A < +105 °C	1.18	1.21	1.24	V
T _{S_vrefint} ⁽¹⁾	ADC sampling time when reading the internal reference voltage	-	10	-	-	μ s
V _{RERINT_s} ⁽²⁾	Internal reference voltage spread over the temperature range	$V_{DD} = 3$ V	-	3	5	mV
T _{Coeff} ⁽²⁾	Temperature coefficient	-	-	30	50	ppm/°C
t _{START} ⁽²⁾	Startup time	-	-	6	10	μ s

1. Shortest sampling time can be determined in the application by multiple iterations.

2. Guaranteed by design.

Table 73. Internal reference voltage calibration values

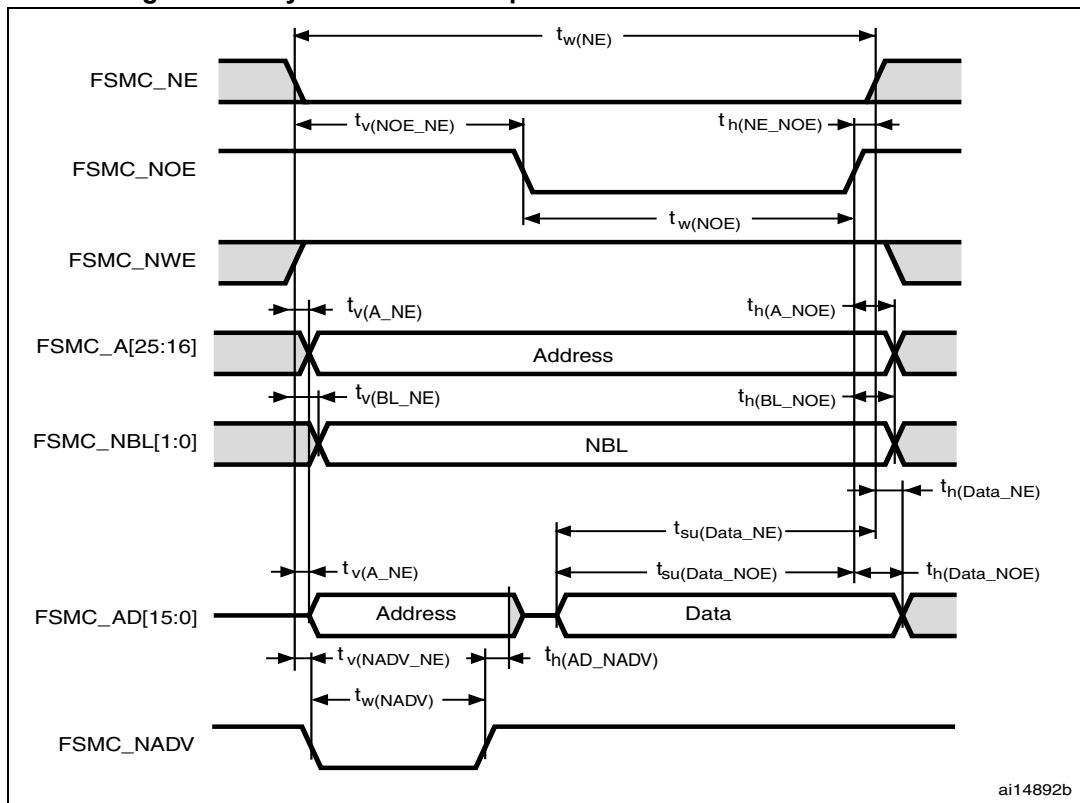
Symbol	Parameter	Memory address
V _{REFIN_CAL}	Raw data acquired at temperature of 30 °C, $V_{DDA}=3.3$ V	0x1FFF 7A2A - 0x1FFF 7A2B

5.3.25 DAC electrical characteristics

Table 74. DAC characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Comments
V _{DDA}	Analog supply voltage	1.8 ⁽¹⁾	-	3.6	V	
V _{REF+}	Reference supply voltage	1.8 ⁽¹⁾	-	3.6	V	$V_{REF+} \leq V_{DDA}$
V _{SSA}	Ground	0	-	0	V	

Figure 56. Asynchronous multiplexed PSRAM/NOR read waveforms



ai14892b

Table 77. Asynchronous multiplexed PSRAM/NOR read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3T_{HCLK}-1$	$3T_{HCLK}+1$	ns
$t_{v(NOE_NE)}$	FSMC_NEx low to FSMC_NOE low	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{w(NOE)}$	FSMC_NOE low time	$T_{HCLK}-1$	$T_{HCLK}+1$	ns
$t_{h(NE_NOE)}$	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
$t_{v(A_NE)}$	FSMC_NEx low to FSMC_A valid	-	3	ns
$t_{v(NADV_NE)}$	FSMC_NEx low to FSMC_NADV low	1	2	ns
$t_{w(NADV)}$	FSMC_NADV low time	$T_{HCLK}-2$	$T_{HCLK}+1$	ns
$t_{h(AD_NADV)}$	FSMC_AD(adress) valid hold time after FSMC_NADV high	T_{HCLK}	-	ns
$t_{h(A_NOE)}$	Address hold time after FSMC_NOE high	$T_{HCLK}-1$	-	ns
$t_{h(BL_NOE)}$	FSMC_BL time after FSMC_NOE high	0	-	ns
$t_{v(BL_NE)}$	FSMC_NEx low to FSMC_BL valid	-	2	ns
$t_{su(Data_NE)}$	Data to FSMC_NEx high setup time	$T_{HCLK}+4$	-	ns
$t_{su(Data_NOE)}$	Data to FSMC_NOE high setup time	$T_{HCLK}+4$	-	ns
$t_{h(Data_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{h(Data_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization.

Table 84. Switching characteristics for PC Card/CF read and write cycles in I/O space⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NIOWR)}$	FSMC_NIOWR low width	$8T_{HCLK} - 1$	-	ns
$t_{v(NIOWR-D)}$	FSMC_NIOWR low to FSMC_D[15:0] valid	-	$5T_{HCLK} - 1$	ns
$t_{h(NIOWR-D)}$	FSMC_NIOWR high to FSMC_D[15:0] invalid	$8T_{HCLK} - 2$	-	ns
$t_{d(NCE4_1-NIOWR)}$	FSMC_NCE4_1 low to FSMC_NIOWR valid	-	$5T_{HCLK} + 2.5$	ns
$t_{h(NCEx-NIOWR)}$	FSMC_NCEx high to FSMC_NIOWR invalid	$5T_{HCLK} - 1.5$	-	ns
$t_{d(NIORD-NCEx)}$	FSMC_NCEx low to FSMC_NIORD valid	-	$5T_{HCLK} + 2$	ns
$t_{h(NCEx-NIORD)}$	FSMC_NCEx high to FSMC_NIORD valid	$5T_{HCLK} - 1.5$	-	ns
$t_{w(NIORD)}$	FSMC_NIORD low width	$8T_{HCLK} - 0.5$	-	ns
$t_{su(D-NIORD)}$	FSMC_D[15:0] valid before FSMC_NIORD high	9	-	ns
$t_{d(NIORD-D)}$	FSMC_D[15:0] valid after FSMC_NIORD high	0	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization.

NAND controller waveforms and timings

[Figure 68](#) through [Figure 71](#) represent synchronous waveforms, and [Table 85](#) and [Table 86](#) provide the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x01;
- COM.FSMC_WaitSetupTime = 0x03;
- COM.FSMC_HoldSetupTime = 0x02;
- COM.FSMC_HiZSetupTime = 0x01;
- ATT.FSMC_SetupTime = 0x01;
- ATT.FSMC_WaitSetupTime = 0x03;
- ATT.FSMC_HoldSetupTime = 0x02;
- ATT.FSMC_HiZSetupTime = 0x01;
- Bank = FSMC_Bank_NAND;
- MemoryDataWidth = FSMC_MemoryDataWidth_16b;
- ECC = FSMC_ECC_Enable;
- ECCPageSize = FSMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Table 87. DCMI characteristics⁽¹⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{su}(DATA)$	Data input setup time	2.5	-	ns
$t_h(DATA)$	Data hold time	1	-	
$t_{su}(HSYNC),$ $t_{su}(VSYNC)$	HSYNC/VSYNC input setup time	2	-	
$t_h(HSYNC),$ $t_h(VSYNC)$	HSYNC/VSYNC input hold time	0.5	-	

1. Guaranteed by characterization.

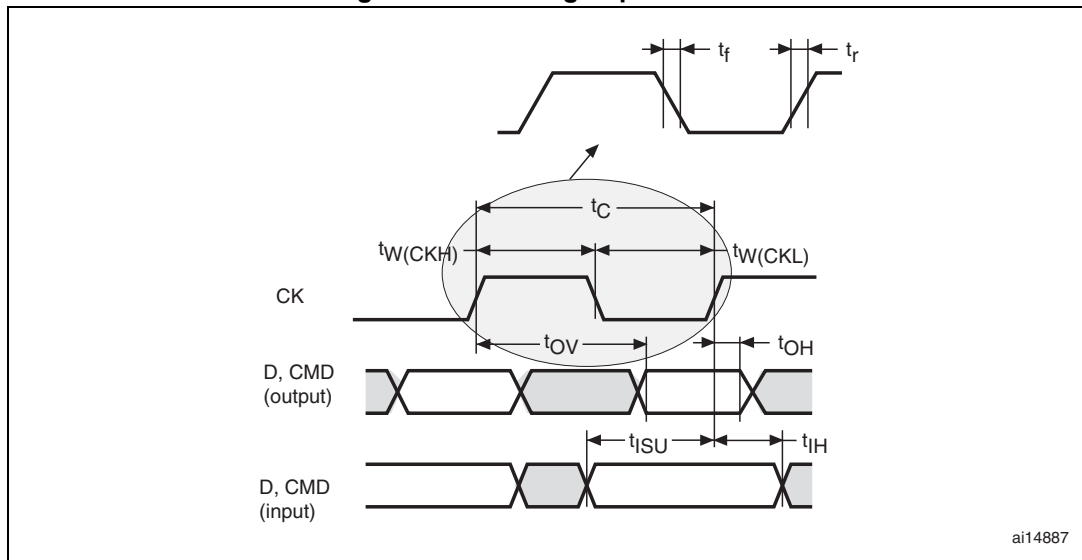
5.3.28 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in [Table 88](#) are derived from tests performed under ambient temperature, f_{PCLKX} frequency and V_{DD} supply voltage conditions summarized in [Table 14](#) with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

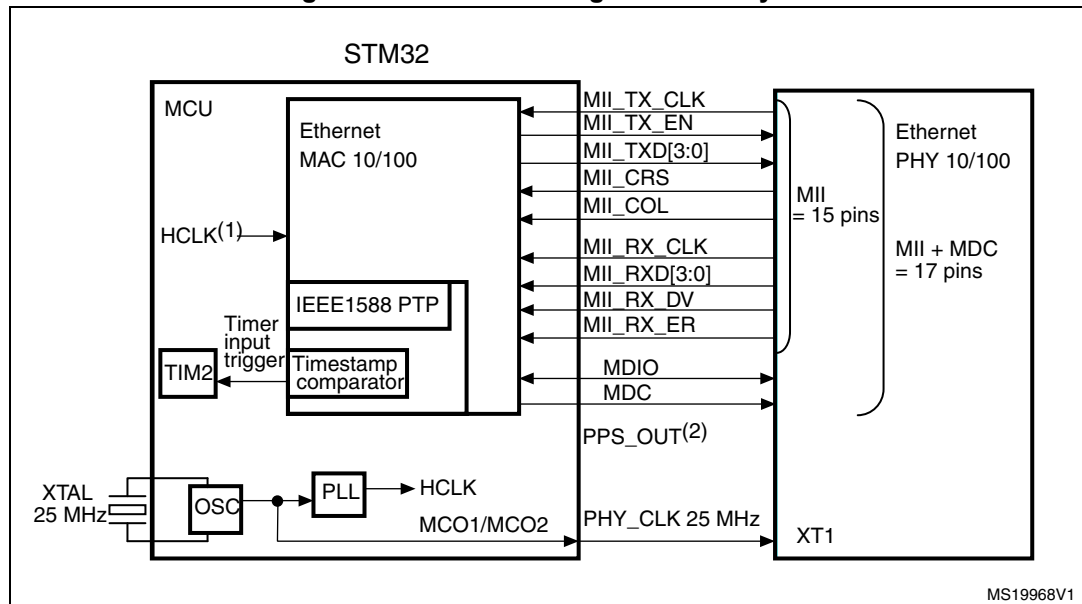
Refer to [Section 5.3.16: I/O port characteristics](#) for more details on the input/output characteristics.

Figure 73. SDIO high-speed mode



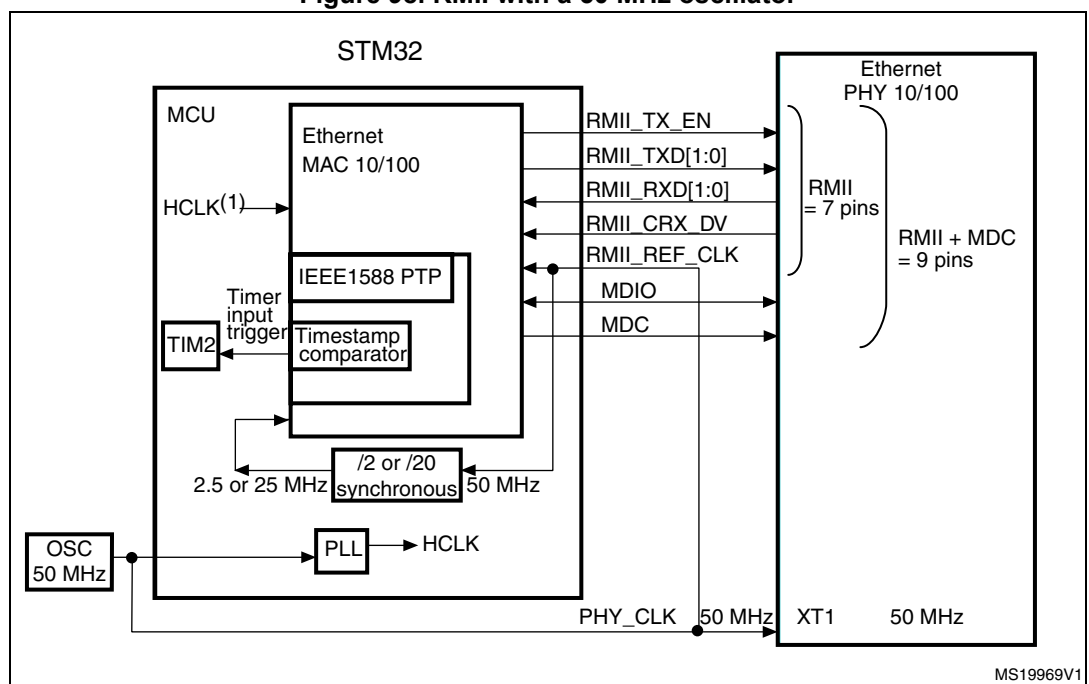
A.3 Ethernet interface solutions

Figure 97. MII mode using a 25 MHz crystal



1. f_{HCLK} must be greater than 25 MHz.
2. Pulse per second when using IEEE1588 PTP optional signal.

Figure 98. RMII with a 50 MHz oscillator



1. f_{HCLK} must be greater than 25 MHz.